L Number	Hits	Search Text	DB	Time stamp
7	910	(aln or aluminum adj nitride) same (MBE or mocvd or hydride adj vapor or hvpe or molecular near2 beam or metal near2 organic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 13:51
8	30	(aln or aluminum adj nitride) same (MBE or molecular near2 beam) near10 (mocvd or metal near2 organic) near10 (hydride near2 vapor or hvpe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 15:15
9	25	(aln or aluminum adj nitride) near10 (MBE or molecular near2 beam) near10 (mocvd or metal near2 organic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 13:53
10	226	(aln or aluminum adj nitride) near10 junction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 15:15
11	21	(aln or aluminum adj nitride) near10 junction near3 pn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 15:23
12	5	(indium adj nitride or inn) near10 junction near3 pn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 15:49
13	111	(zno or zinc adj oxide) near5 buffer same (gan or gallium adj nitride or "iii-v")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 15:50
14	2	(zno or zinc adj oxide) near5 buffer near10 amorphous same (gan or gallium adj nitride or "iii-v")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 15:51
15	2	"11243229"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 15:58
16	45	(zno or zinc adj oxide) near10 (polycrystal$5) same varistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 16:21
17	3	(zno or zinc adj oxide) near5 buffer same pn near2 junction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 16:22
18	985	junction near10 (gan or gallium adj nitride or "iii-v")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 16:23
19	29	(junction near10 (gan or gallium adj nitride or "iii-v")) same (zno or zinc adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 16:26
20	3	"04068579"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 16:59

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21	2	tetsuzo near2 ueda.in. and spin near2 coat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 16:59
-	34	spin near5 coat$3 same (anneal$4 or heat adj treat$4 or crystalliz$4 or rta or rtp) and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:02
-	0	(III-V or nitride) near5 solution same anneal$4 same crystalliz$4 and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:04
-	2	(III-V or nitride) near5 solution same crystalliz$4 and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:05
-	15	(III-V or nitride) near5 solution same film and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:11
-	209	solution near10 (crystal$4 or crystalliz$4) same film and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:25
-	4	solution near10 (crystal$4 or crystalliz$4) same film same "III-V" and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:28
-	13	solution near10 (crystal$4 or crystalliz$4) same film same "nitride" and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:30
-	2	nitride near10 solution same (anneal$ or rapid adj thermal or heat adj treat$4 or rta or rtp or ptp) and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:31
-	667	nitride near10 solution same (anneal$ or rapid adj thermal or heat adj treat$4 or rta or rtp or ptp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:32
-	0	nitride near10 solution same (anneal$ or rapid adj thermal or heat adj treat$4 or rta or rtp or ptp) same (crystal$4 or crystalliz$4) same spin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:32
-	90	nitride near10 solution same (anneal$ or rapid adj thermal or heat adj treat$4 or rta or rtp or ptp) same (crystal$4 or crystalliz$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:32
-	0	nitride near10 solution same (anneal$ or rapid adj thermal or heat adj treat$4 or rta or rtp or ptp) same (crystal$4 or crystalliz$4) same "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:32
-	3	"iii-v" near10 solution same (anneal$ or rapid adj thermal or heat adj treat$4 or rta or rtp or ptp) same (crystal$4 or crystalliz$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:55

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-	444946	anneal$ or rapid adj thermal or heat adj treat$4 or rta or rtp or ptp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:55
-	37679	spin near4 coat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:56
-	3	((spin near4 coat$4) same ("IIi-v" or "III" near4 nitride)) same (anneal$ or rapid adj thermal or heat adj treat$4 or rta or rtp or ptp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 11:56
-	46	(spin near4 coat$4) same ("IIi-v" or "III" near4 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:24
-	4	heat$4 near10 ligand same "III-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:26
-	0	solution near10 ligand same "III-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:26
-	1	solution near10 heat$4 near10 (volatile or vaporiz$4) same "III-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:27
-	65	solution near10 heat$4 near10 (volatile or vaporiz$4) and spin near4 coat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:28
-	6	solution near10 heat$4 near10 (volatile or vaporiz$4) same spin near4 coat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:29
-	77	spin near4 coat$4 same ("iii-v" or "iii" near3 nitride or gan or gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:31
-	42	spin near4 coat$4 same ("iii-v" or "iii" near3 nitride or gan or gallium adj nitride) not same (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:44
-	6	("5433169" | "5923950" | "5989338" | "5997639" | "6146457" | "6176925").PN.	USPAT	2003/09/22 13:35
-	96	("iii-v" or "iii" near3 nitride or gan or gallium adj nitride) same (crystal$4 or crystalliz$4 or crystalline) same precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:45
-	38	("iii-v" or "iii" near3 nitride or gan or gallium adj nitride) same (crystal$4 or crystalliz$4 or crystalline) near10 precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:47
-	10	("iii-v" or "iii" near3 nitride or gan or gallium adj nitride) same (crystal$4 or crystalliz$4 or crystalline) near10 precursor same solution	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/22 13:47

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–	87	spin near2 coat$5 same ("iii-v" or gan or gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 14:22
–	2090	(gan or gallium adj nitride) near4 buffer near5 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 14:22
–	143	(gan or gallium adj nitride) near4 buffer near5 (layer or film) same (aluminum adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 14:22
–	33	(gan or gallium adj nitride) adj buffer near5 (layer or film) same (aluminum adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 14:24
–	35	(gan or gallium adj nitride) adj buffer near5 (layer or film) same (inn indium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 14:30
–	16	(gan or gallium adj nitride) adj buffer near5 (layer or film) same (indium or aluminum) near10 thick$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 14:41
–	2	"0999640"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 14:35
–	5	"999640"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 14:35
–	0	(gan or gallium adj nitride) adj buffer near5 (layer or film) same (indium or aluminum) same pn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 14:45
–	7	(gan or gallium adj nitride) adj buffer near5 (layer or film) same pn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 15:21
–	27	(aluminum adj nitride or aln) near10 pn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 15:24
–	67	spin near2 coat$5 same (aluminum adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 15:26
–	10	spin near2 coat$5 near15 (aluminum adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 15:26